

BCR12PM-12LC

Triac

Medium Power Use

REJ03G1261-0100

Rev.1.00

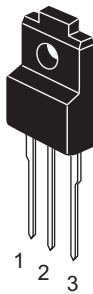
Sep.28.2005

Features

- $I_{T(RMS)}$: 12 A
- V_{DRM} : 600 V
- I_{FGTI} , I_{RGTI} , I_{RGTHI} : 50 mA
- V_{ISO} : 1500 V
- The product guaranteed maximum junction temperature 150°C.
- Insulated Type
- Planar Passivation Type

Outline

RENESAS Package code: PRSS0003AA-B
(Package name: TO-220F(2))



1. T₁ Terminal
2. T₂ Terminal
3. Gate Terminal

Applications

Heater control, motor control

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	700	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_T (RMS)$	12	A	Commercial frequency, sine full wave 360° conduction, $T_c = 87^\circ C$
Surge on-state current	I_{TSM}	72	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	21.6	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	A	
Junction temperature	T_j	- 40 to +125	$^\circ C$	
Storage temperature	T_{stg}	- 40 to +125	$^\circ C$	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	1500	V	$T_a = 25^\circ C$, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	I_{DRM}	—	—	2.0	mA	$T_j = 125^\circ C$, V_{DRM} applied
On-state voltage	V_{TM}	—	—	1.8	V	$T_c = 25^\circ C$, $I_{TM} = 20 A$, Instantaneous measurement
Gate trigger voltage ^{Note2}	I	V_{FGTI}	—	—	1.5	$T_j = 25^\circ C$, $V_D = 6 V$, $R_L = 6 \Omega$, $R_G = 330 \Omega$
	II	V_{RGTI}	—	—	1.5	
	III	V_{RGTIII}	—	—	1.5	
Gate trigger current ^{Note2}	I	I_{FGTI}	—	—	50	$T_j = 25^\circ C$, $V_D = 6 V$, $R_L = 6 \Omega$, $R_G = 330 \Omega$
	II	I_{RGTI}	—	—	50	
	III	I_{RGTIII}	—	—	50	
Gate non-trigger voltage	V_{GD}	0.2	—	—	V	$T_j = 125^\circ C$, $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	3.7	$^\circ C/W$	Junction to case ^{Note3}
Critical-rate of rise of off-state commutating voltage ^{Note4}	$(dv/dt)_c$	10	—	—	$V/\mu s$	$T_j = 125^\circ C$

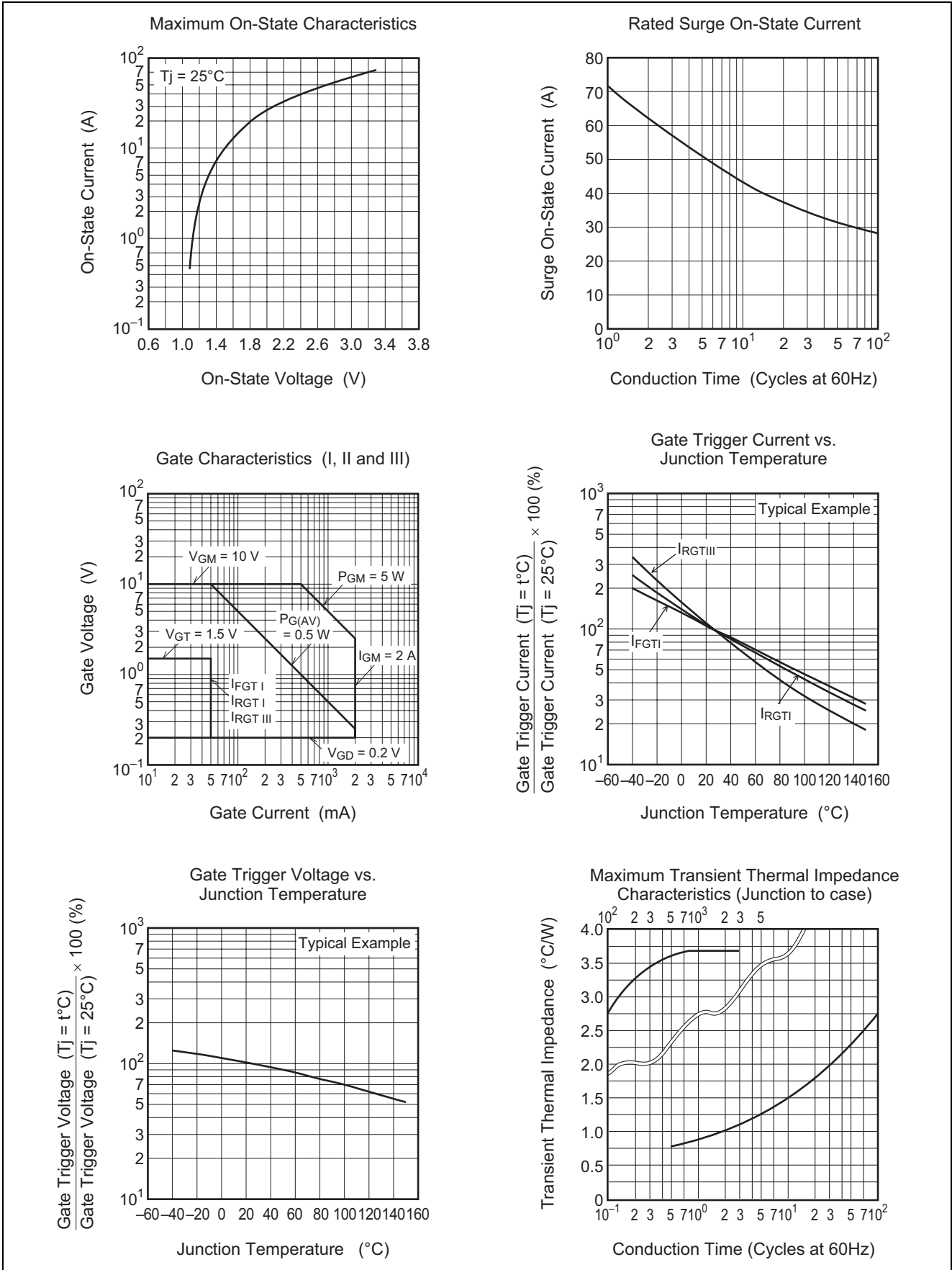
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance $R_{th(c-f)}$ in case of greasing is $0.5^\circ C/W$.

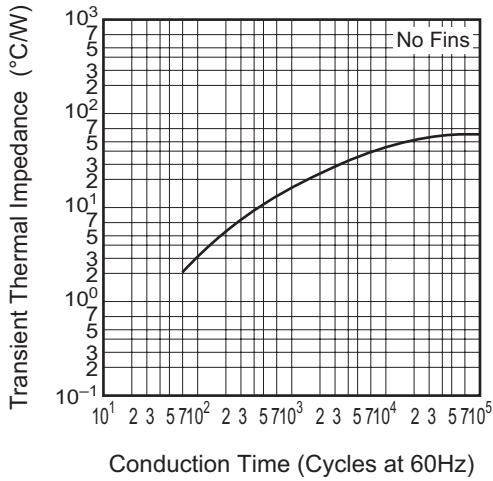
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ C$ 2. Rate of decay of on-state commutating current $(di/dt)_c = - 6 A/ms$ 3. Peak off-state voltage $V_D = 400 V$	

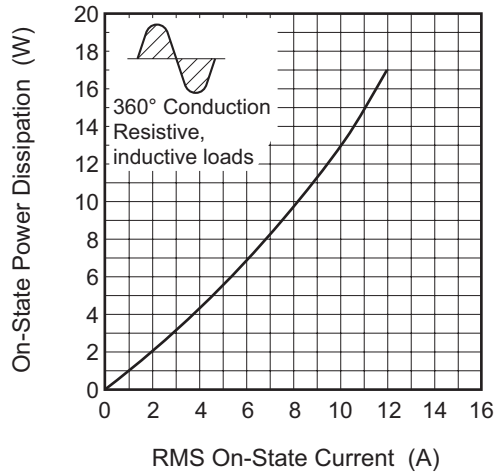
Performance Curves



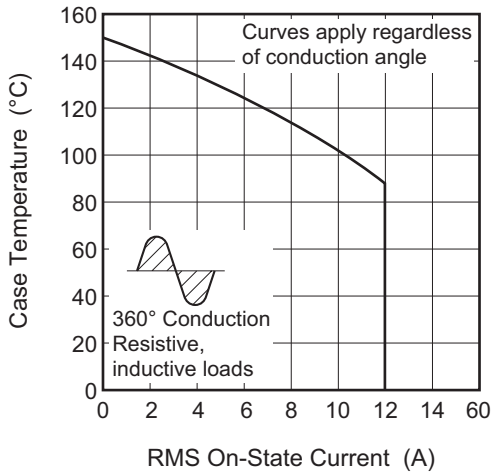
Maximum Transient Thermal Impedance Characteristics (Junction to ambient)



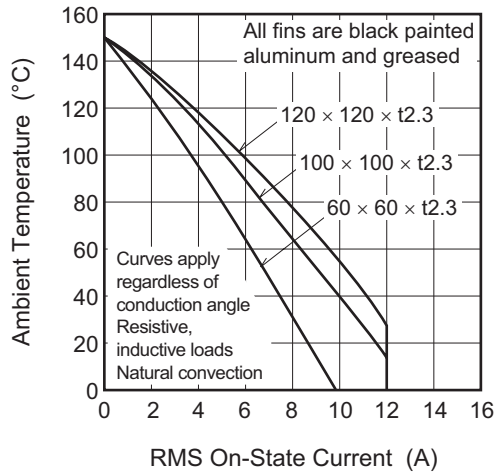
Maximum On-State Power Dissipation



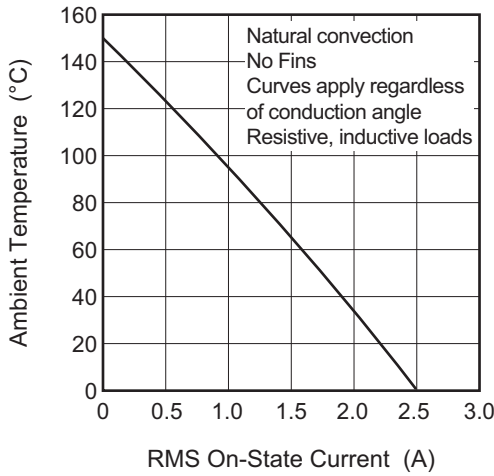
Allowable Case Temperature vs. RMS On-State Current



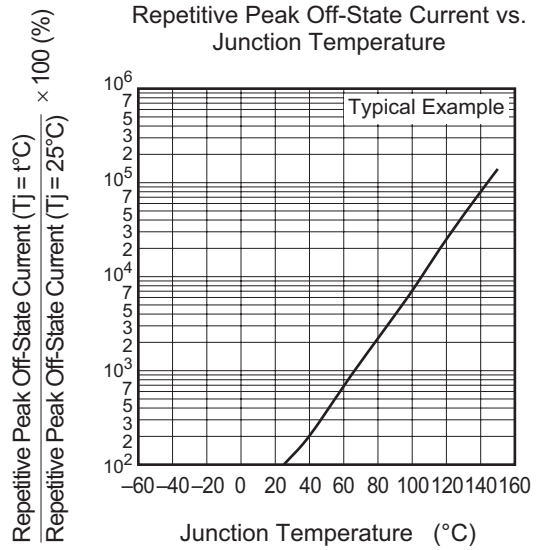
Allowable Ambient Temperature vs. RMS On-State Current



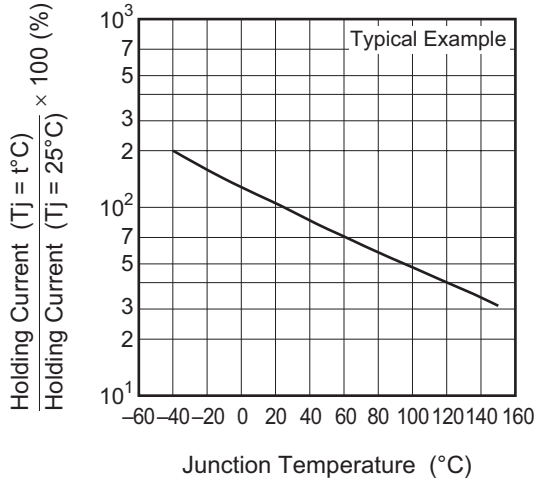
Allowable Ambient Temperature vs. RMS On-State Current



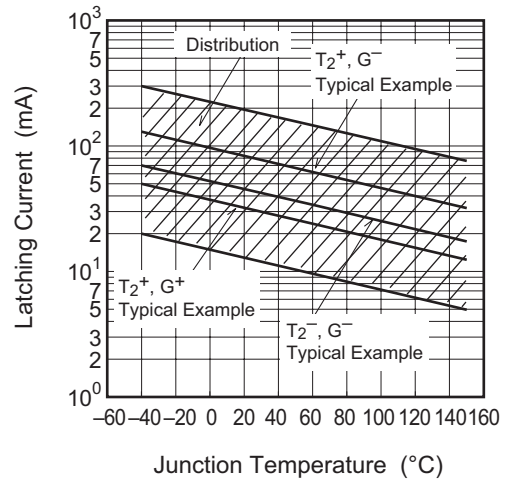
Repetitive Peak Off-State Current vs. Junction Temperature



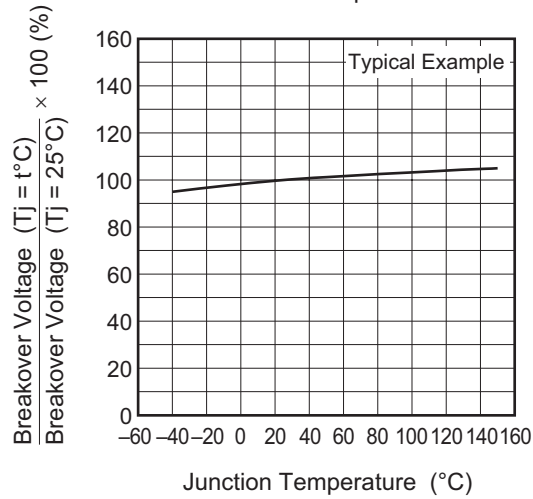
Holding Current vs. Junction Temperature



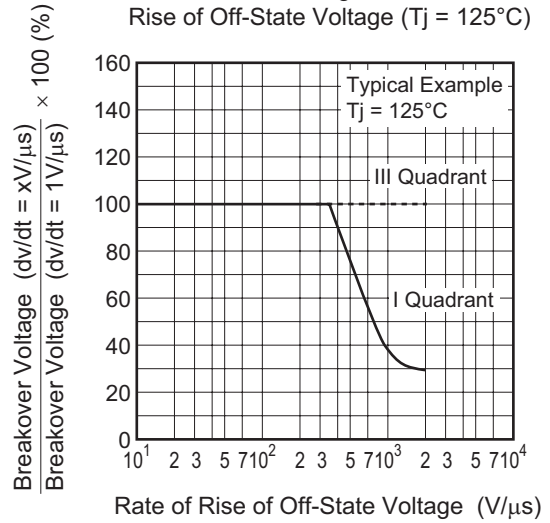
Latching Current vs. Junction Temperature



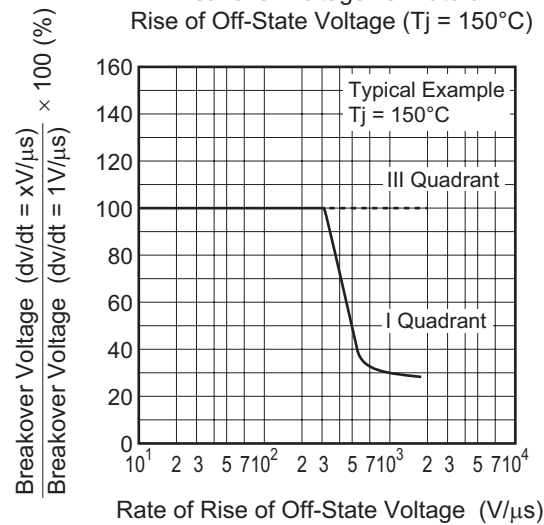
Breakover Voltage vs. Junction Temperature



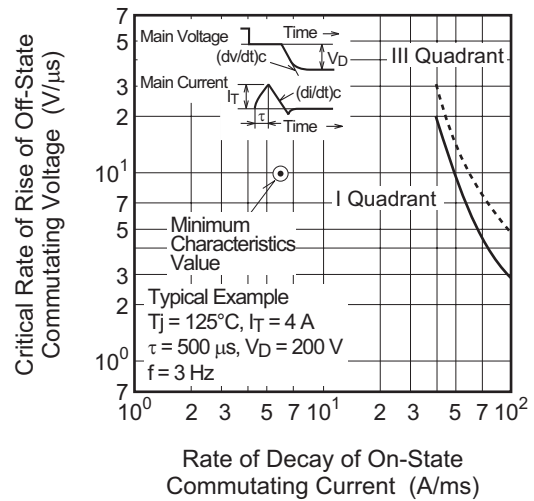
Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj = 125°C)

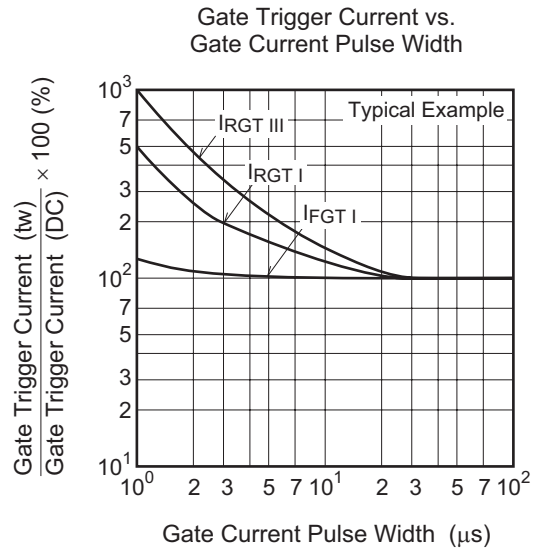
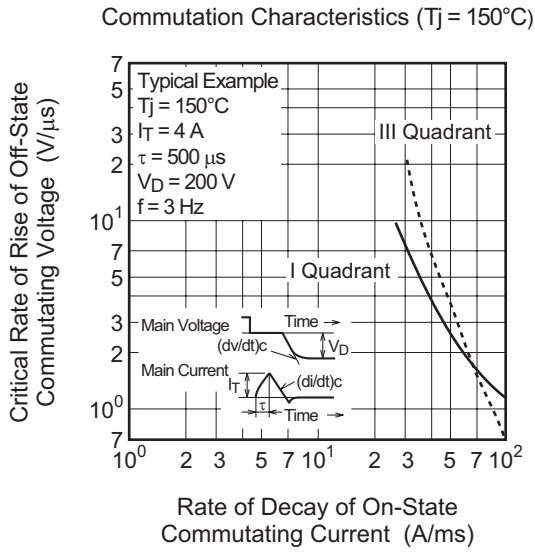


Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj = 150°C)

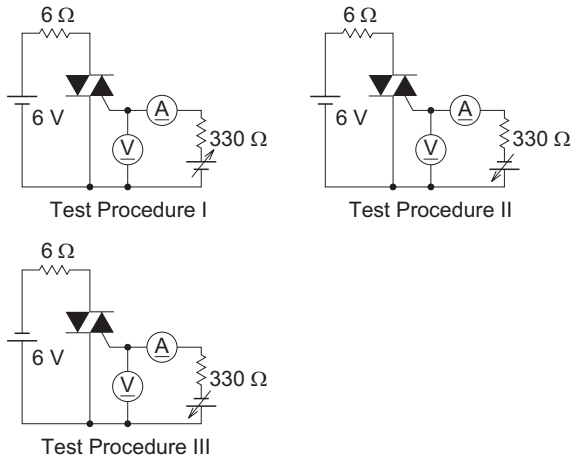


Commutation Characteristics (Tj = 125°C)

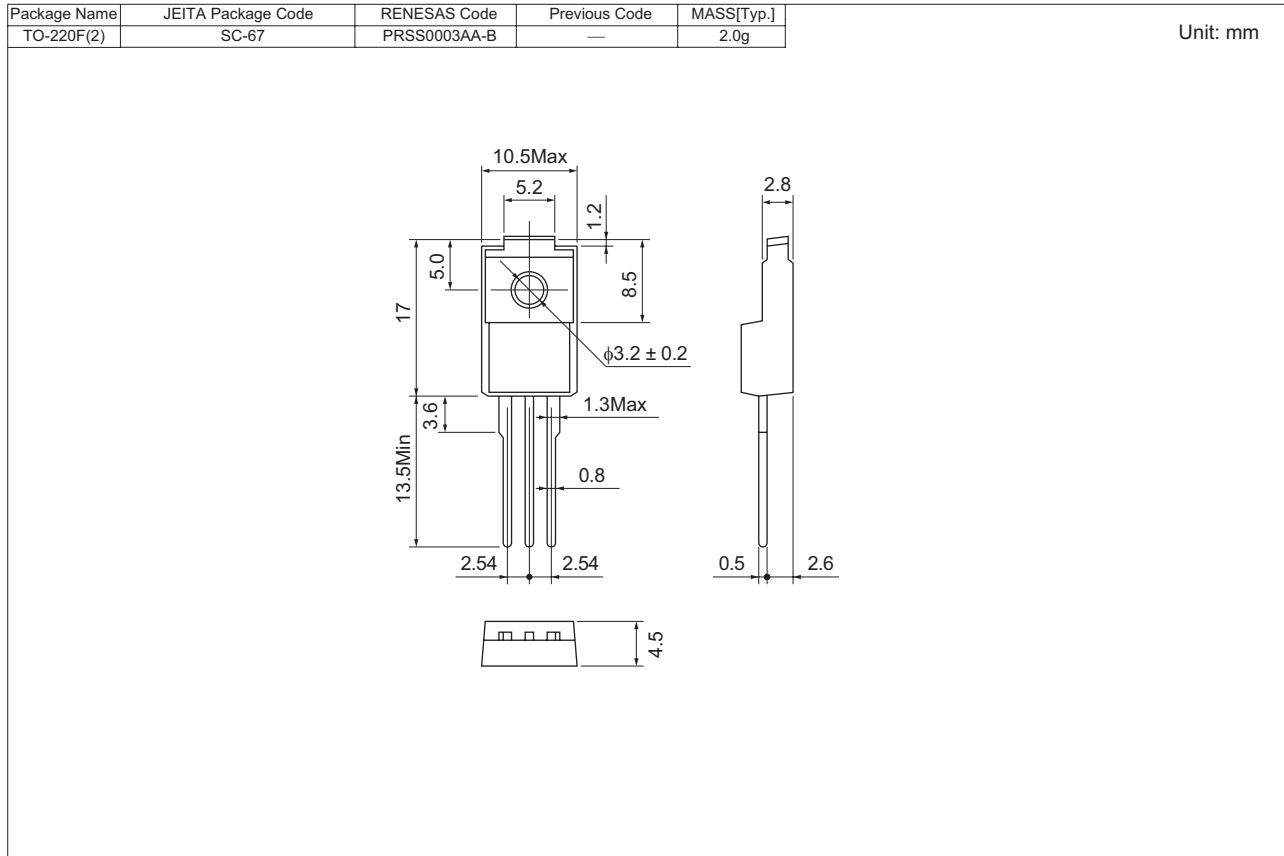




Gate Trigger Characteristics Test Circuits



Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR12PM-12LC
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR12PM-12LC-A8

Note : Please confirm the specification about the shipping in detail.

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